

B1 cont  
said first electrode layer including at least one selected from a first metal group consisting of Ti, Hf, Zr, Nb, Ta and Sc,

said second electrode layer including at least one selected from a second metal group consisting of Ni, Pd and Co, and Ni / Au

said third electrode layer including Au.

B2 Pub C1  
8. (Amended) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

said first electrode layer including at least one selected from a first metal group consisting of Ti, Hf, Zr, Nb, Ta and Sc,

said second electrode layer including at least one selected from a second metal group consisting of Ni and Co, and

said third electrode layer including Au.

Please add new claims 12-14 as follows:

B3 Sub D1  
12. The electrode structure according to claim 8, wherein said first electrode layer includes a nitride of a metal included in said first metal group, and also includes a compound of Ga and a metal included in said second metal group.

13. An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,

3  
B cont

said first electrode layer having a thickness of 10 to 500 nm and including at least one selected from a first metal group consisting of Ti, Hf, Zr, Nb, Ta and Sc,

said second electrode layer having a thickness of 50 nm or more and including at least one selected from a second metal group consisting of Ni, Pd and Co, and

said third electrode layer having a thickness of 50 nm or more and including Au.

14. The electrode structure according to claim 13, wherein said first electrode layer includes a nitride of a metal included in said first metal group, and also includes a compound of Ga and a metal included in said second metal group.

---